Features

- Trench Power LV MOSFET technology
- AEC-Q101 Qualified
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-CHANNEL MOSFET

Maximum Ratings

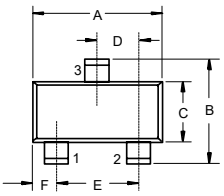
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 96°C/W Junction to Ambient(Note 2)

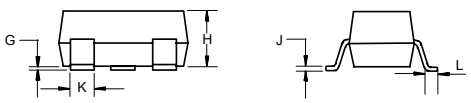
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-4.1	A
	T_A=70°C		-3.2	
Pulsed Drain Current(Note 3)		I_{DM}	-12	A
Total Power Dissipation(Note 4)		P_D	1.3	W

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. Pd is based on max. junction temperature, using junction-case thermal resistance.

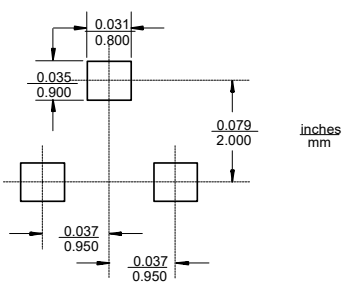
SOT-23



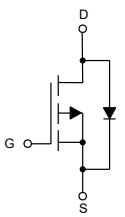


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

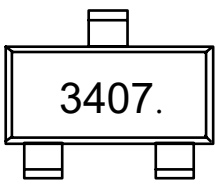
Suggested Solder Pad Layout



Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.5	-2.4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-4.1A		36	49	mΩ
		V_{GS}=-4.5V, I_D=-3.2A		52	65	
Diode Characteristics						
Continuous Body Diode Current	I_S				-4.1	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-4.1A			-1.2	V
Reverse Recovery Time	t_{rr}	I_S=-2.2A,di/dt=100A/μs		12		ns
Reverse Recovery Charge	Q_{rr}			3.6		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V,f=1MHz		592		pF
Output Capacitance	C_{oss}			73		
Reverse Transfer Capacitance	C_{rss}			63		
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-10V,I_D=-4.1A		13		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			2.2		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=15V,V_G=10V, R_G=4.5Ω, I_D=20A		6.2		ns
Turn-On Rise Time	t_r			3.8		
Turn-Off Delay Time	$t_{d(off)}$			23		
Turn-Off Fall Time	t_f			9.4		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

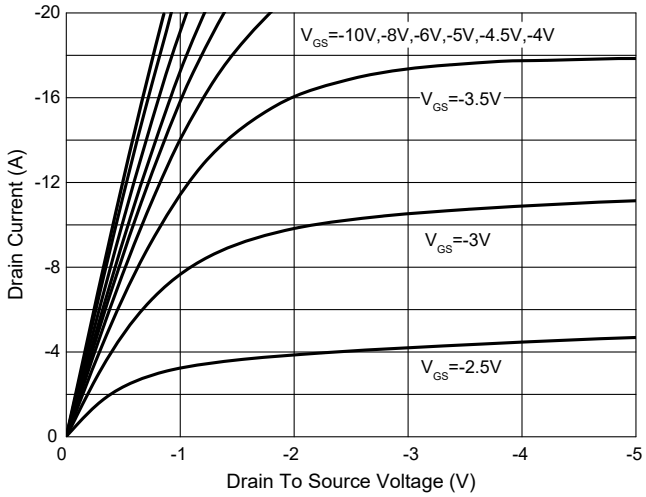


Fig. 2 - Transfer Characteristics

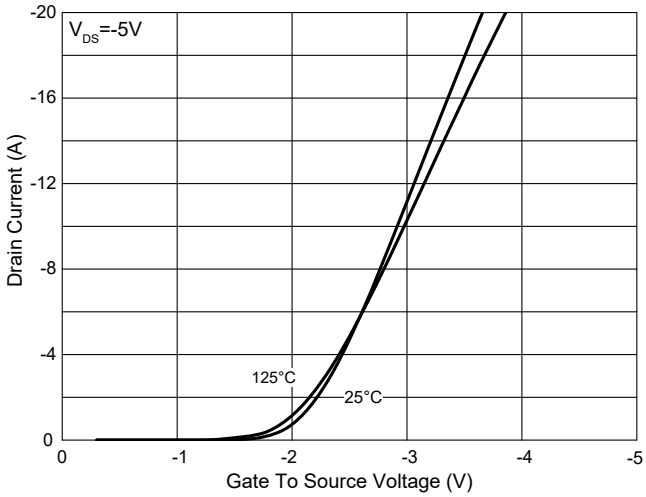


Fig. 3 - $R_{DS(ON)}$—V_{GS}

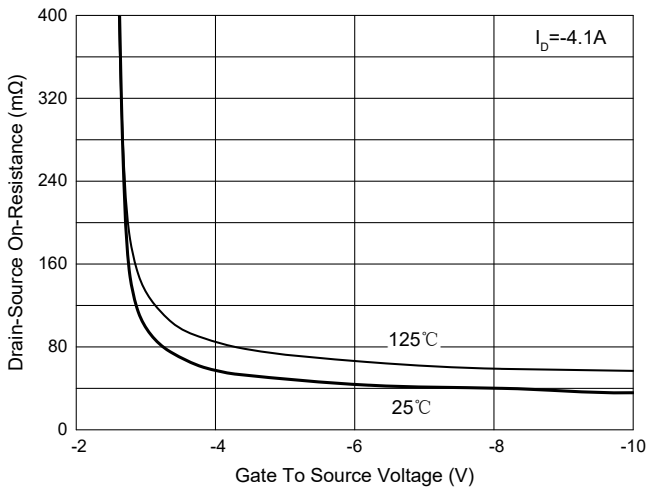


Fig. 4 - $R_{DS(ON)}$—I_D

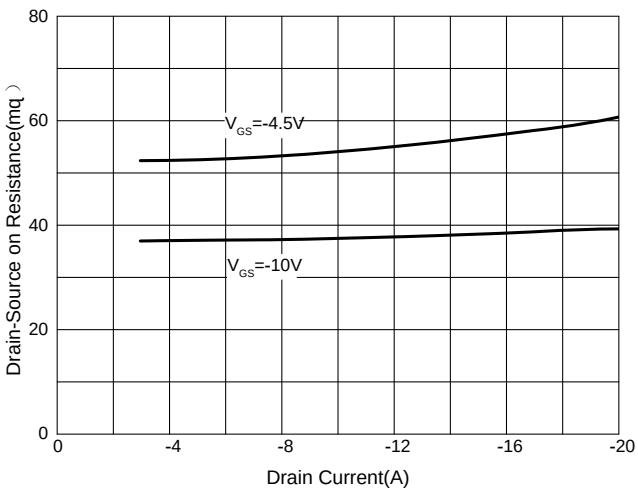


Fig. 5 - Capacitance Characteristics

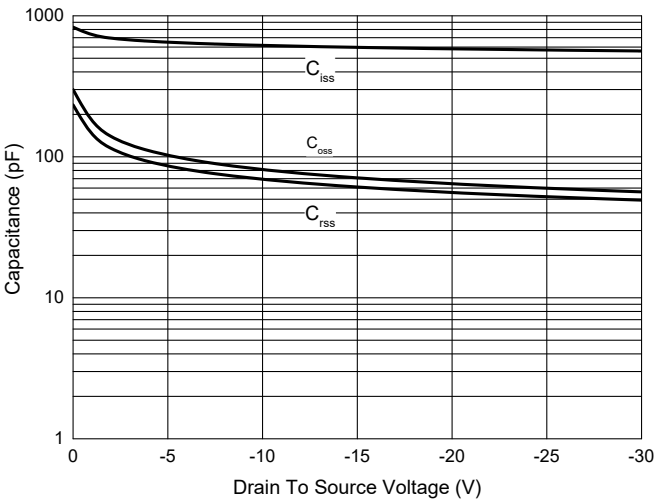
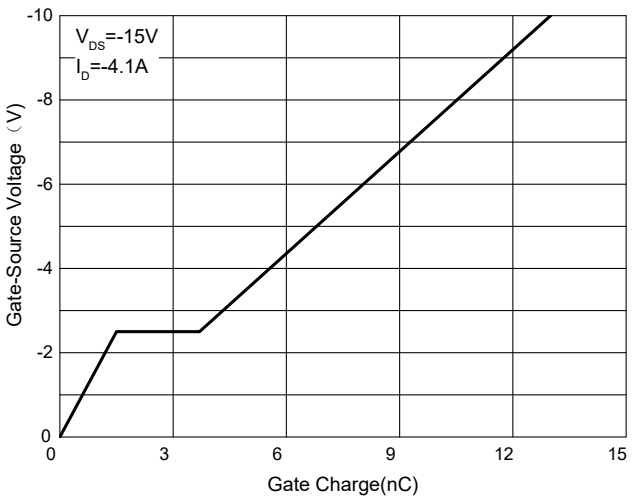


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Nomalized Threshold Voltage

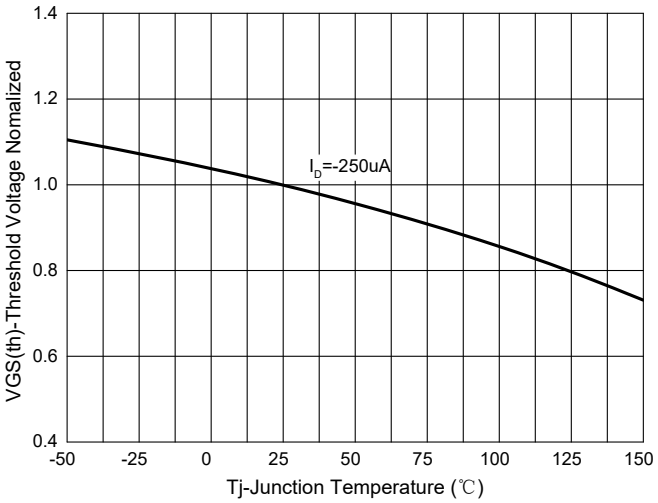


Fig.8-Normalized On Resistance Characteristics

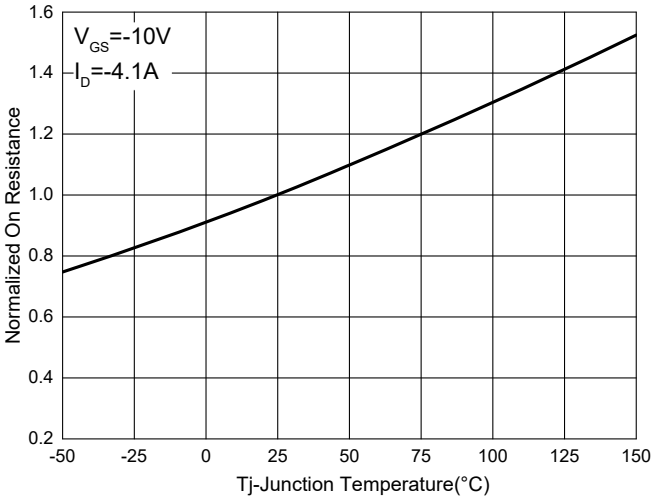


Fig.9 - I_S—V_{SD}

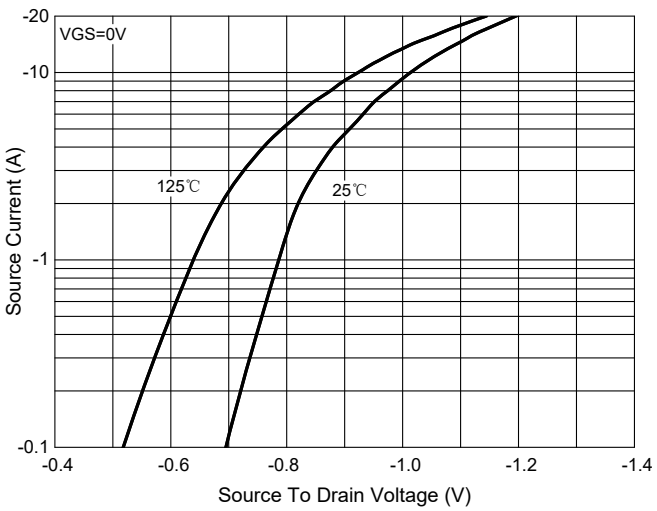


Fig. 10 - Drain Current

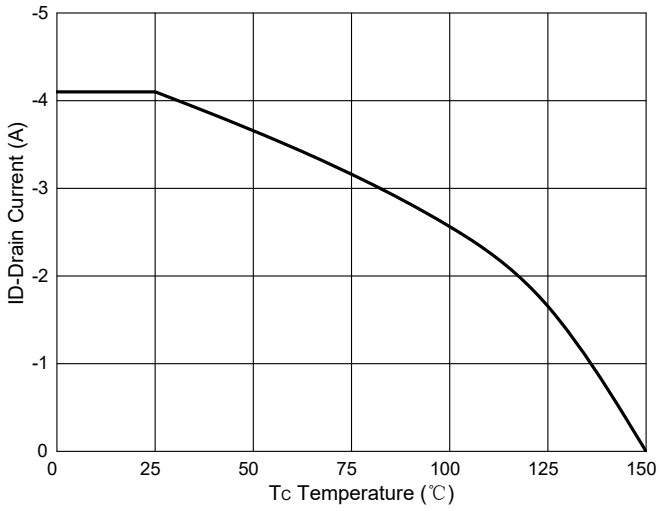
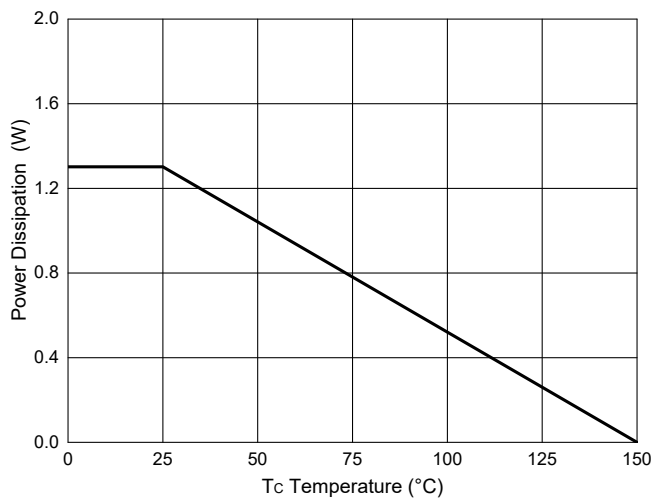


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

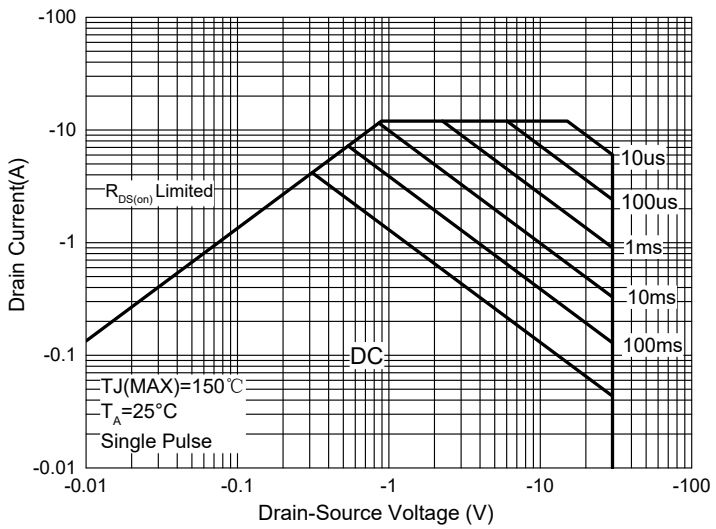
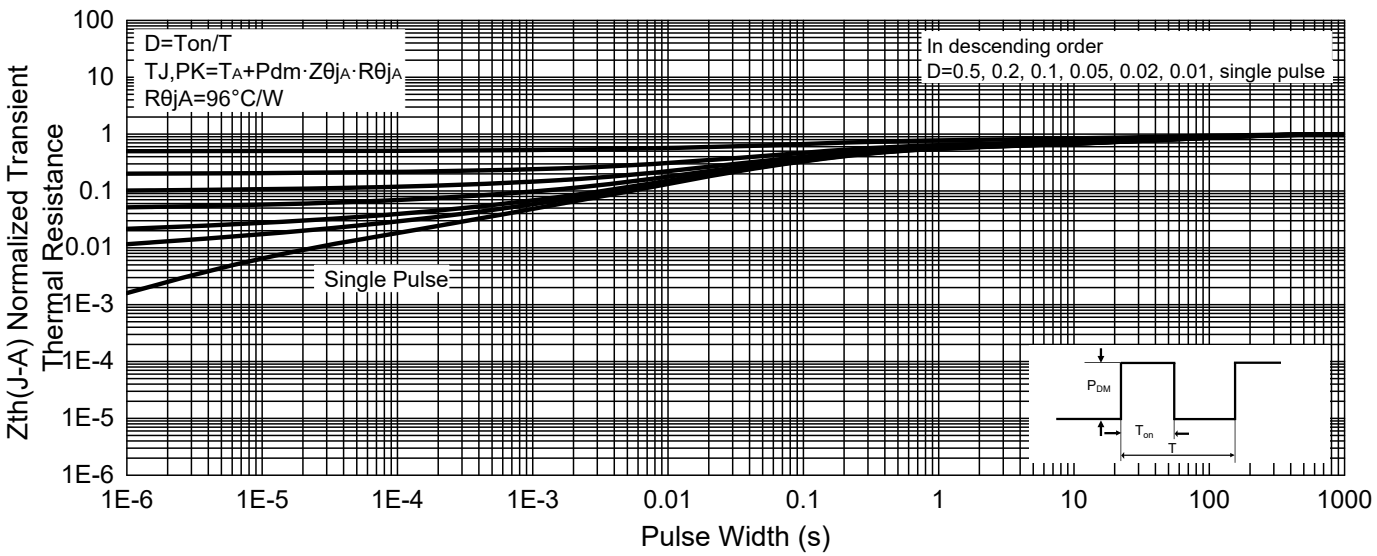


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
SI3407HE3-TP	Tape&Reel: 3Kpcs/Reel